# **Current Transducers HAS 50 to 600-S**

For the electronic measurement of currents: DC, AC, pulsed, mixed, with a galvanic isolation between the primary circuit (high power) and the secondary circuit (electronic circuit).





#### **Electrical data**

Primary nomin r.m.s. current I <sub>PN</sub> (A)	al Primary current measuring range I <sub>P</sub> (A)	Туре		
50 100 200 300 400 500 600		HAS 50-S HAS 100-S HAS 200-S HAS 300-S HAS 400-S HAS 500-S HAS 600-S		
$\begin{array}{c} \mathbf{V}_{c} \\ \mathbf{I}_{c} \\ \mathbf{I}_{oc} \\ \mathbf{V}_{d} \\ \mathbf{V}_{b} \\ \mathbf{R}_{ls} \\ \mathbf{V}_{OUT} \\ 40 \\ \mathbf{R}_{OUT} \\ \mathbf{R}_{L} \end{array}$	Supply voltage (± 5 %) Current consumption Overload capacity R.m.s. voltage for AC isolar R.m.s. rated voltage, safe s Isolation resistance @ 500 Output voltage @ $\pm I_{PN}$ , $R_{L} =$ Output internal resistance Load resistance	separation VDC	± 15 ± 15 30,000 3 500 <sup>1)</sup> > 1000 100 > 1	V mA kV kV ν MΩ ± 4V ± Ω kΩ

## Accuracy - Dynamic performance data

-, -,			
Accuracy @ $I_{PN}$ , $T_{A} = 25^{\circ}C$ (	without offset)	<±1	%
Linearity <sup>2)</sup> $(0 \dots \pm \hat{I}_{PN})$		<±1	% of $I_{_{\rm PN}}$
Electrical offset voltage, $T_{A} = 25^{\circ}C$		< ± 20	mV
Hysteresis offset voltage $\hat{\mathbf{Q}} \mathbf{I}_{p} = 0;$			
after an excursion of 1 x I		< ± 20	mV
	HAS 50-S	<±2	mV/K
ŬL.	HAS 100 to HAS 600-S	< ± 1	mV/K
Thermal drift of the gain (% of reading)		< ± 0.1	%/K
Response time @ 90% of	I <sub>D</sub>	< 3	μs
di/dt accurately followed		> 50	Aμs
Frequency bandwidth (- 3 c	dΒ) <sup>3)</sup>	DC 50	) kHz
l data			
Ambient operating tempera	ature	- 10 +	80 °C
, <b>e</b> 1		- 25 +	80 °C
Mass		. 60	g
Standards <sup>4)</sup>		EN 501	
	Accuracy ( $ \mathbf{I}_{PN}, \mathbf{T}_{A} = 25^{\circ}C ($ Linearity <sup>2)</sup> (0± $\mathbf{I}_{PN}$ ) Electrical offset voltage, $\mathbf{T}_{A}$ Hysteresis offset voltage ( $ \mathbf{G} $ after an excursion of 1 x $\mathbf{I}_{PN}$ Thermal drift of $\mathbf{V}_{OE}$ Thermal drift of the gain (% Response time ( $ \mathbf{G} $ 90% of di/dt accurately followed Frequency bandwidth (- 3 of <b>I data</b> Ambient operating temperation Ambient storage temperation Mass	Electrical offset voltage, $\mathbf{T}_{A} = 25^{\circ}$ C Hysteresis offset voltage $\mathbf{Q} \ \mathbf{I}_{p} = 0$ ; after an excursion of 1 x $\mathbf{I}_{pN}$ Thermal drift of $\mathbf{V}_{OE}$ HAS 50-S HAS 100 to HAS 600-S Thermal drift of the gain (% of reading) Response time @ 90% of $\mathbf{I}_{p}$ di/dt accurately followed Frequency bandwidth (- 3 dB) <sup>3</sup> <b>I data</b> Ambient operating temperature Ambient storage temperature Mass approx	Accuracy @ $I_{PN}$ , $T_A = 25^{\circ}C$ (without offset)< ± 1

 $I_{PN} = 50..600 \text{ A}$  $V_{OUT} = \pm 4 \text{ V}$ 



## Features

- Hall effect measuring principle
- Galvanic isolation between primary and secondary circuit
- Isolation voltage 3000 V~
- Low power consumption
- Extended measuring range  $(3 \times I_{_{PN}})$
- Insulated plastic case made of polycarbonate PBT recognized according to UL 94-V0

### **Advantages**

- Easy mounting
- Small size and space saving
- Only one design for wide current ratings range
- High immunity to external interference.

# Applications

- AC variable speed drives
- Static converters for DC motor drives
- Battery supplied applications
- Uninterruptible Power Supplies (UPS)
- Switched Mode Power Supplies (SMPS)
- Power supplies for welding applications.

Notes : <sup>1)</sup> Pollution class 2, overvoltage category III.

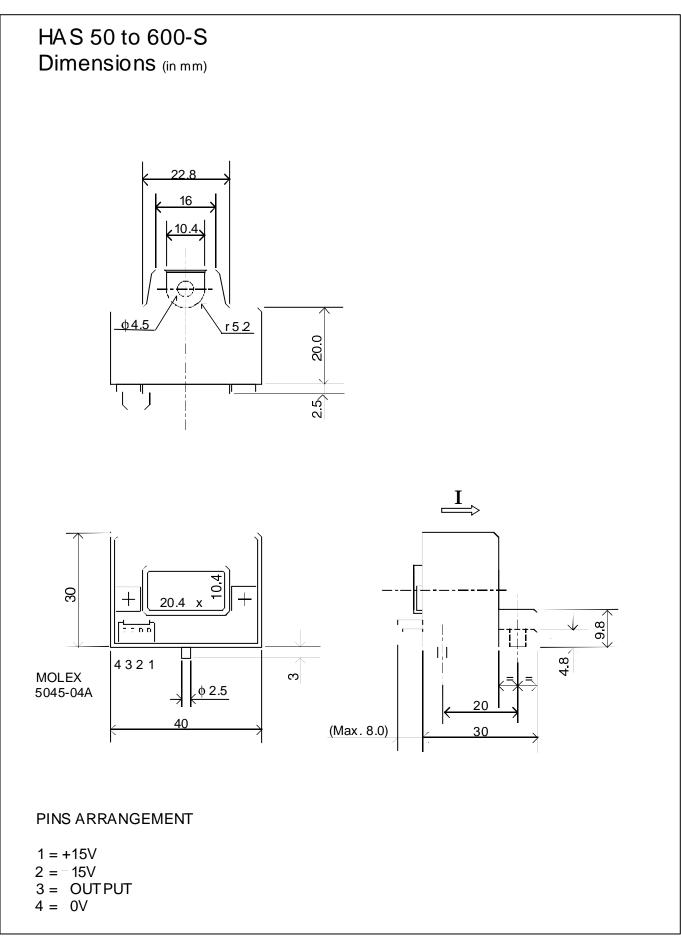
- <sup>2)</sup> Linearity data exclude the electrical offset.
- <sup>3)</sup> Please refer to derating curves in the technical file to avoid excessive core heating at high frequency.

<sup>4)</sup> Please consult characterisation report for more technical details and application advice.

LEM Components

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LEM reserves the right to change limits and dimensions.

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Datasheets for electronics components.